Cypress Semiconductor
Qualification Report

QTP# 98115 VERSION 1.0
July, 1998

1 Meg SRAM, R42HD Technology (5V operation)	
CY7C1021	64K x 16 Static RAM
CY7C1019	128K x 8 Static RAM

CYPRESS TECHNICAL CONTACT FOR QUALIFICATION DATA:

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Reliability Manager
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PRODUCT DESCRIPTION (for qualification)	
Qualification Purpose: Qualify 1Meg SRAM in qualified technology R42HD	
Marketing Part #:	CY7C1021
Package:	44-pin, 400-mil SOJ
Device Description:	64K x 16 Static RAM, R42HD Technology
Cypress Division:	Cypress Semiconductor Corporation
Overall Die (or Mask) REV Level (pre-requisite for qualification):	Rev. E
What ID markings on Die:	7C1021A

TECHNOLOGY/FAB PROCESS DESCRIPTION - R42HD			
Number of Metal Layers:	2	Metal Composition:	Metal 1: 500Å TiW/6000Å Al -5%Cu/1200Å TiW Metal 2: 500Å TiW/8000Å Al -5%Cu/300Å TiW
Passivation Type and Materials:	7000Å SiO_2 + 6000Å Si_3N_4		
Free Phosphorus contents in top glass layer(%):	0%		
Die Coating(s), if used:	N/A		
Generic Process Technology/Design Rule (µ-drawn):	CMOS, Double Metal /0.42 µm		
Gate Oxide Material/Thickness (MOS):	SiO_2 / 110Å		
Name/Location of Die Fab (prime) Facility:	Cypress Semiconductor - Bloomington, MN		
Die Fab Line ID/Wafer Process ID:	Fab4/R4HD		

PLASTIC PACKAGE/ASSEMBLY DESCRIPTION			
Package Outline, Type, or Name:	44-pin, 400-mil SOJ		
Mold Compound Name/Manufacturer:	Hitachi-9200		
Lead Frame material:	Copper Alloy 194		
Lead Finish, composition:	Solder Plated, 90%Sn, 10%Pb		
Die Attach Area Plating:	Silver Spot		
Die Attach Method:	Epoxy	Die Attach Material:	Ablestik 8361
Wire Bond Method:	Gold Ball bond	Wire Material/Size:	Gold / 1.3 mil
JESD22-A112 Moisture Sensitivity Level:	Level 3		
Name/Location of Assembly (prime) facility:	Cypress Bangkok, Thailand (CSPI-R)		

Note: Please contact a Cypress Representative for other packages availability.

RELIABILITY TESTS PERFORMED

Stress/Test	Test Condition (Temp/Bias)	Result P/F
Temperature Cycle	MIL-STD-883C, Method 1010, Condition C, -65°C to 150°C Precondition: JESD22 Moisture Sensitivity Level 3 (192 Hrs, 30C/60%RH)	P
Electrostatic Discharge Human Body Model (ESD-HBM)	MIL-STD-883, Method 3015.7	2,200V
Electrostatic Discharge Charge Device Model (ESD-CDM)	Cypress Spec. 25-00020	1,000V
Latchup Sensitivity	In accordance with JEDEC 17. Cypress Spec. 01-00081	
Static Latchup		11.1V
Dynamic Latchup		7.2V
Pressure Cooker Test (PCT)	121C/100%RH	P

RELIABILITY FAILURE RATE SUMMARY

Stress/Test	Device Tested/ Device Hours	# Fails	Activation Energy	Thermal AF[4]	Failure Rate
High Temperature Operating Life Early Failure Rate[1]	N/A	NA	N/A	N/A	N/A
High Temperature Operating Life[2,3] Long Term Failure Rate	392,500 DHRs (98248)	0	0.7	170	14 FIT
	791,500 DHRs (98064)	0	0.7	170	7 FIT

[1] A production burn-in of 48 Hrs at 135°C, 6.5V is required for the product.
[2] Assuming an ambient temperature of 55°C and a junction temperature rise of 15°C.
[3] Chi-squared 60% estimations used to calculate the failure rate. Long term failure rate is based on R42HD, Fab 4, 1 Meg (qtp 98064) and 4 Meg (qtp 98248) SRAM qualifications.
[4] Thermal Acceleration Factor is calculated from the Arrhenius equation.

$$AF = \exp\left[\frac{E_A}{k}\left[\frac{1}{T_2} - \frac{1}{T_1}\right]\right]$$

where:

E_A =The Activation Energy of the defect mechanism.
k = Boltzmann's constant = 8.62×10^{-5} eV/Kelvin.
T_1 is the junction temperature of the device under stress and T_2 is the junction temperature of the device at use conditions.

RELIABILITY TEST DATA

QTP#: 98115

DEVICE	ASSY-LOC	FABLOT#	ASSYLOT#	DURATION	S/S	REJ	FAIL MODE
STRESS: DYNAMIC LATCH-UP TESTING (8.2V)							
CY7C1021-VC	CSPI-R	4812391	619804711	DATA	3	0	
STRESS: ESD-CHARGE DEVICE MODEL (1000V)							
7C1019EC-OVCB	INDNS-O	4812391	519805462	COMP	3	0	
CY7C1021-VC	CSPI-R	4812391	619804711	DATA	3	0	
STRESS: ESD-HUMAN BODY CIRCUIT PER MIL STD 883, METHOD 3015 (2200V)							
CY7C1021-VC	CSPI-R	4812391	619804711	DATA	3	0	
STRESS: PRESSURE COOKER TEST (121C, 100%RH)							
CY7C1021-VC	CSPI-R	4812391	619804711	96	50	0	
CY7C1021-VC	CSPI-R	4812391	619804711	168	50	0	
STRESS: DYNAMIC LATCH-UP TESTING (11.1V)							
CY7C1021-VC	CSPI-R	4812391	619804711	DATA	3	0	
STRESS: TC COND. C, -65 TO 150C, PRECOND. 192 HRS 30C/60%RH (MSL 3)							
CY7C1021-VC	CSPI-R	4812391	619804711	300	50	0	

DEVICE RELATED RELIABILITY TEST DATA

QTP#: 98248[1]

DEVICE	ASSY-LOC	FABLOT#	ASSYLOT#	DURATION	S/S	REJ	FAIL MODE
STRESS: ALPHA SENSITIVITY							
CY7C1049-VC	SEOL-L	4750331	619800740	DATA	5	0	
STRESS: STATIC LATCH-UP TESTING (125C / 7.5V)							
CY7C1049-VC	SEOL-L	4750331	619800740	DATA	3	0	
STRESS: DYNAMIC LATCH-UP TESTING (11.2V)							
CY7C1049-VC	SEOL-L	4750331	619800740	DATA	3	0	
STRESS: ESD-CHARGE DEVICE MODEL (1000V)							
CY7C1049-VC	SEOL-L	4750331	619800740	COMP	3	0	
STRESS: ESD-HUMAN BODY CIRCUIT PER MIL STD 883, METHOD 3015 (2200V)							
CY7C1049-VC	SEOL-L	4750331	619800740	COMP	3	0	
STRESS: HI-ACCEL SATURATION TEST (140C, 5.5V), PRECOND. 168 HRS 85C/85%RH							
CY7C1049-VC	SEOL-L	4750331	619800740	128	47	0	
STRESS: HIGH TEMP STEADY STATE LIFE TEST (150C, 5.5V)							
CY7C1049-VC	SEOL-L	4750331	619800740	80	79	0	1 EOS
CY7C1049-VC	SEOL-L	4750331	619800740	168	79	0	
CY7C1049-VCB	SEOL-L	4750364	619801747	168	80	0	
CY7C1049-VCB	SEOL-L	4750364	619801747	80	80	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE (150C, 5.75V)							
CY7C1049-VC	SEOL-L	4750331	619800740	80	385	0	
CY7C1049-VC	SEOL-L	4750331	619800740	500	385	0	
CY7C1049-VCB	SEOL-L	4750364	619801747	80	400	0	
CY7C1049-VCB	SEOL-L	4750364	619801747	500	400	0	
STRESS: READ & RECORD (150C, 5.75V)							
CY7C1049-VC	SEOL-L	4750331	619800740	500	12	0	
CY7C1049-VCB	SEOL-L	4750364	619801747	500	12	0	
STRESS: TC COND. C, -65 TO 150C, PRECOND. 192 HRS 30C/60%RH (MSL 3)							
CY7C1049-VC	SEOL-L	4750331	619800740	300	47	0	
CY7C1049-VCB	SEOL-L	4750364	619801747	300	48	0	
CY7C1049-VCB	SEOL-L	4752513	619802812L1	300	47	0	

[1] QTP 98248, 4 Meg SRAM, R42HD, Fab 4 qualification.

DEVICE RELATED RELIABILITY TEST DATA

QTP#: 98064[2]

DEVICE	ASSY-LOC	FABLOT#	ASSYLOT#	DURATION	S/S	REJ	FAIL MODE
STRESS: ESD-CHARGE DEVICE MODEL, 1000V							
CY7C109-VC	INDNS-O	4738602	519712560	COMP	3	0	
STRESS: ESD-HUMAN BODY CIRCUIT PER MIL STD 883, METHOD 3015, 2200V							
CY7C109-VC	INDNS-O	4738602	519712560	COMP	3	0	
STRESS: HI-ACCEL SATURATION TEST (140C, 5.5V), PRECOND. 192 HRS 30C/60%RH							
CY7C109-VC	INDNS-O	4738602	519712560	128	46	0	
CY7C109-VC	INDNS-O	4738564	519712898	128	46	0	
CY7C109-VC	INDNS-O	4738564	519712898	256	46	0	
CY7C109-VC	INDNS-O	4739644	519714390	128	46	0	
STRESS: HIGH TEMPERATURE STORAGE (165C, NO BIAS)							
CY7C109-VC	INDNS-O	4738602	519712560	336	46	0	
CY7C109-VC	INDNS-O	4738602	519712560	500	46	0	
CY7C109-VC	INDNS-O	4738602	519712560	1000	46	0	
STRESS: HIGH TEMP STEADY STATE LIFE TEST (150C, 5.75V)							
CY7C109-VC	INDNS-O	4738602	519712560	80	78	0	
CY7C109-VC	INDNS-O	4738602	519712560	168	78	0	
CY7C109-VC	INDNS-O	4739644	519714390	80	78	0	
CY7C109-VC	INDNS-O	4739644	519714390	168	78	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE (150C, 5.75V)							
CY7C109-VC	INDNS-O	4739644	519714390	80	528	0	
CY7C109-VC	INDNS-O	4739644	519714390	500	527	0	
CY7C109-VC	INDNS-O	4745042	519800651L1	80	529	0	
CY7C109-VC	INDNS-O	4745042	519800651L1	500	529	0	
STRESS: EXTENDED DYNAMIC BURN-IN (150C, 5.75V)							
CY7C109-VC	INDNS-O	4739644	519714390	1000	527	0	
STRESS: COLD LIFE TEST (-30C, 6.5V)							
CY7C109-VC	INDNS-O	4738602	519712560	500	45	0	
CY7C109-VC	INDNS-O	4738602	519712560	1000	45	0	
STRESS: READ & RECORD LIFE TEST (150C, 5.75V)							
CY7C109-VC	INDNS-O	4738602	519712560	48	10	0	
CY7C109-VC	INDNS-O	4738602	519712560	500	10	0	
STRESS: TC COND. C, -65 TO 150C, PRECOND. 192 HRS 30C/60%RH							
CY7C109-VC	INDNS-O	4738602	519712560	300	46	0	
CY7C109-VC	INDNS-O	4738602	519712560	1000	46	0	
CY7C109-VC	INDNS-O	4738564	519712898	300	46	0	
CY7C109-VC	INDNS-O	4739644	519714390	300	46	0	

[2] QTP98064, 1 Meg SRAM, R42HD Technology, Fab 4 qualification.